

### Applications

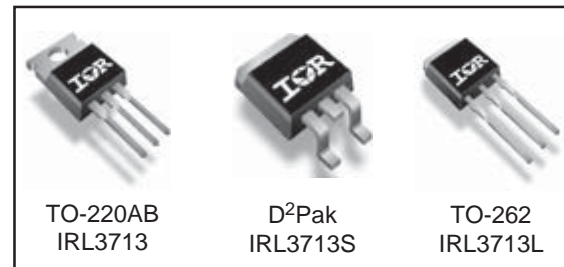
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power
- 100%  $R_G$  Tested

HEXFET® Power MOSFET

$V_{DS}$	$R_{DS(on)}$ max (m $\Omega$ )	$I_D$
30V	3.0 @ $V_{GS} = 10V$	260A <sup>⑥</sup>

### Benefits

- Ultra-Low Gate Impedance
- Very Low  $R_{DS(on)}$  at 4.5V  $V_{GS}$
- Fully Characterized Avalanche Voltage and Current



### Absolute Maximum Ratings

Symbol	Parameter	Max	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$ @ $T_C = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	260 <sup>⑥</sup>	A
$I_D$ @ $T_C = 100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	180 <sup>⑥</sup>	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	1040 <sup>⑥</sup>	
$P_D$ @ $T_C = 25^\circ C$	Maximum Power Dissipation	330	W
$P_D$ @ $T_C = 100^\circ C$	Maximum Power Dissipation	170	
	Linear Derating Factor	2.2	W/ $^\circ C$
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to +175	$^\circ C$

### Thermal Resistance

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Junction-to-Case <sup>②</sup>	—	0.45	$^\circ C/W$
$R_{qCS}$	Case-to-Sink, Flat, Greased Surface <sup>④</sup>	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient <sup>④⑦</sup>	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) <sup>⑤⑦</sup>	—	40	

Notes <sup>①</sup> through <sup>⑦</sup> are on page 11

**Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.027	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.6	3.0	m $\Omega$	$V_{GS} = 10V, I_D = 38A$ ③
		—	3.3	4.0		$V_{GS} = 4.5V, I_D = 30A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	50	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	20		$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

**Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$g_{fs}$	Forward Transconductance	76	—	—	S	$V_{DS} = 15V, I_D = 30A$
$Q_g$	Total Gate Charge	—	75	110	nC	$I_D = 30A$
$Q_{gs}$	Gate-to-Source Charge	—	24	—		$V_{DS} = 15V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	37	—		$V_{GS} = 4.5V$ ④
$Q_{oss}$	Output Gate Charge	—	61	92		$V_{GS} = 0V, V_{DS} = 15V$
$R_G$	Gate Resistance	0.5	—	3.4	$\Omega$	
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 15V$
$t_r$	Rise Time	—	160	—		$I_D = 30A$
$t_{d(off)}$	Turn-Off Delay Time	—	40	—		$R_G = 1.8\Omega$
$t_f$	Fall Time	—	57	—		$V_{GS} = 4.5V$ ③
$C_{iss}$	Input Capacitance	—	5890	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	3130	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	630	—		$f = 1.0\text{MHz}$

**Avalanche Characteristics**

Symbol	Parameter	Typ	Max	Units
$E_{AS}$	Single Pulse Avalanche Energy ②	—	1530	mJ
$I_{AR}$	Avalanche Current ①	—	46	A

**Diode Characteristics**

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	260 ⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①⑥	—	—	1040 ⑥		
$V_{SD}$	Diode Forward Voltage	—	0.80	1.3	V	$T_J = 25^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
		—	0.68	—		$T_J = 125^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	75	110	ns	$T_J = 25^\circ\text{C}, I_F = 30A, V_R = 0V$
$Q_{rr}$	Reverse Recovery Charge	—	140	210	nC	$di/dt = 100A/\mu s$ ③
$t_{rr}$	Reverse Recovery Time	—	78	120	ns	$T_J = 125^\circ\text{C}, I_F = 30A, V_R = 20V$
$Q_{rr}$	Reverse Recovery Charge	—	160	240	nC	$di/dt = 100A/\mu s$ ③

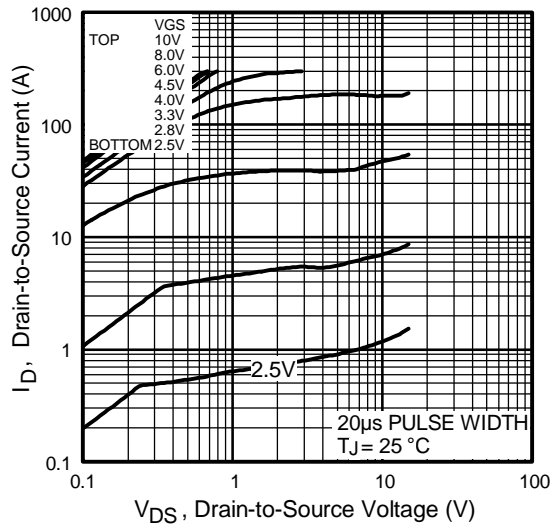


Fig 1. Typical Output Characteristics

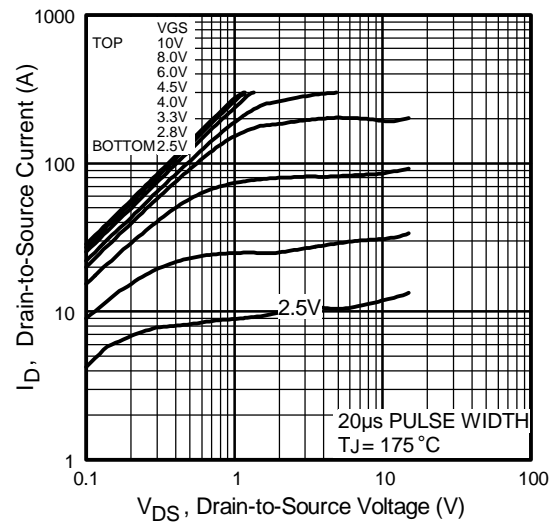


Fig 2. Typical Output Characteristics

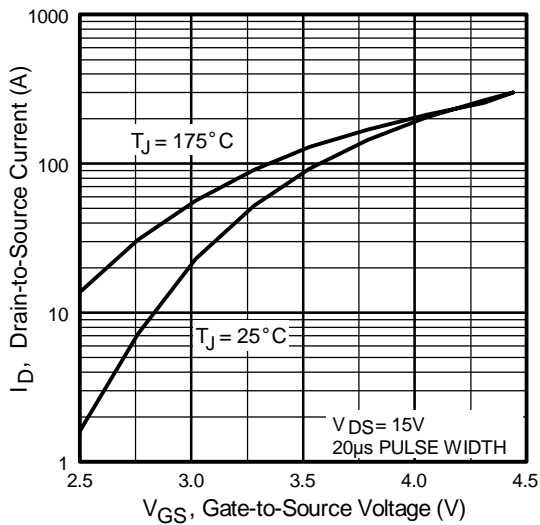


Fig 3. Typical Transfer Characteristics

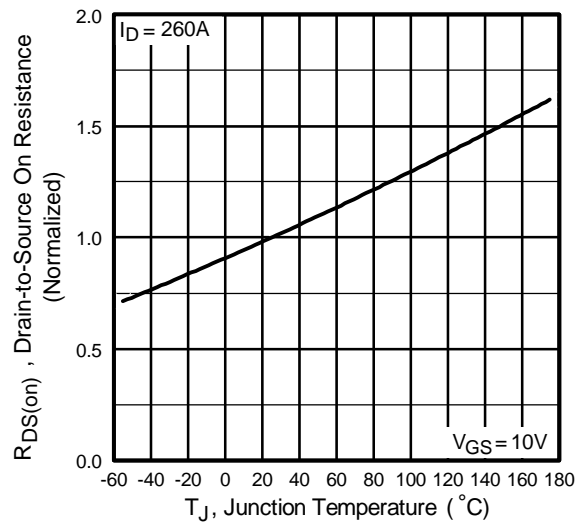
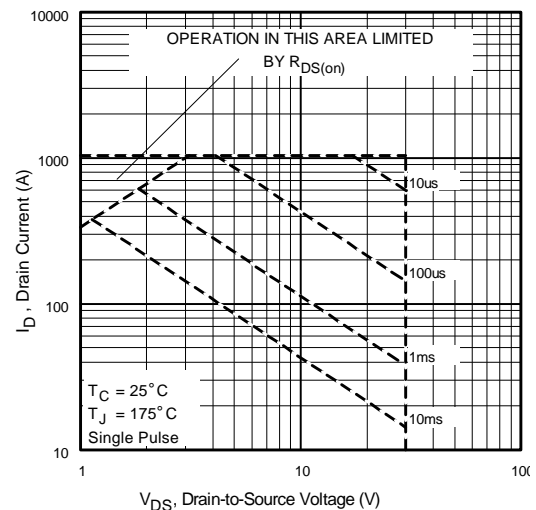
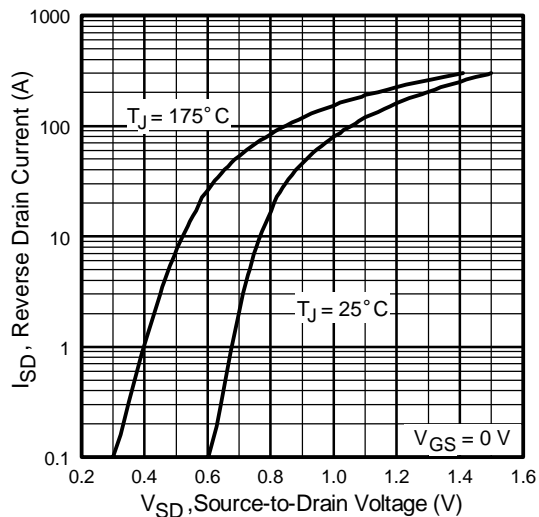
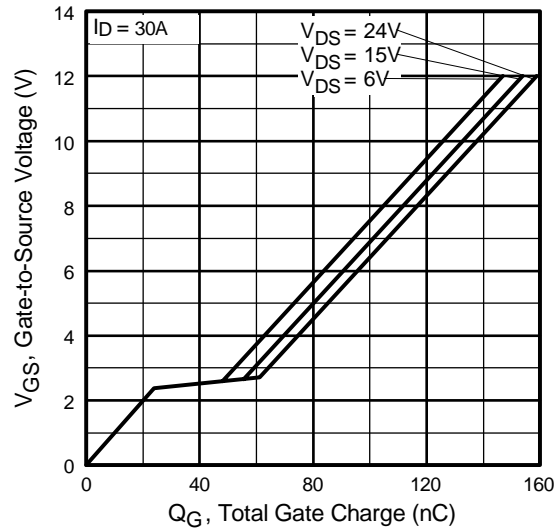
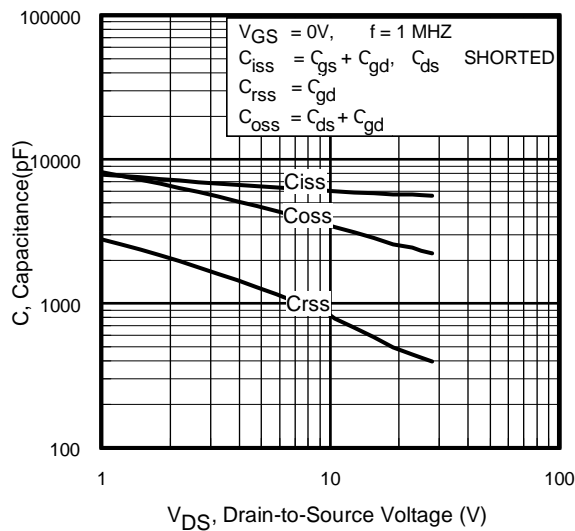
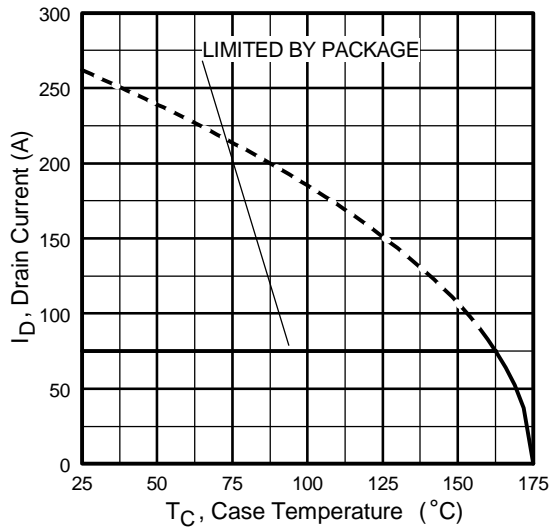
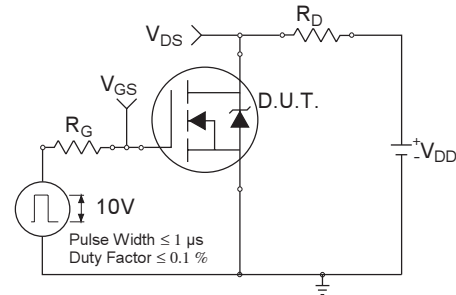


Fig 4. Normalized On-Resistance Vs. Temperature

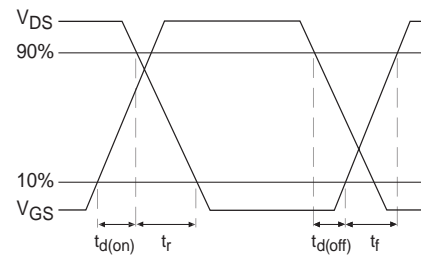




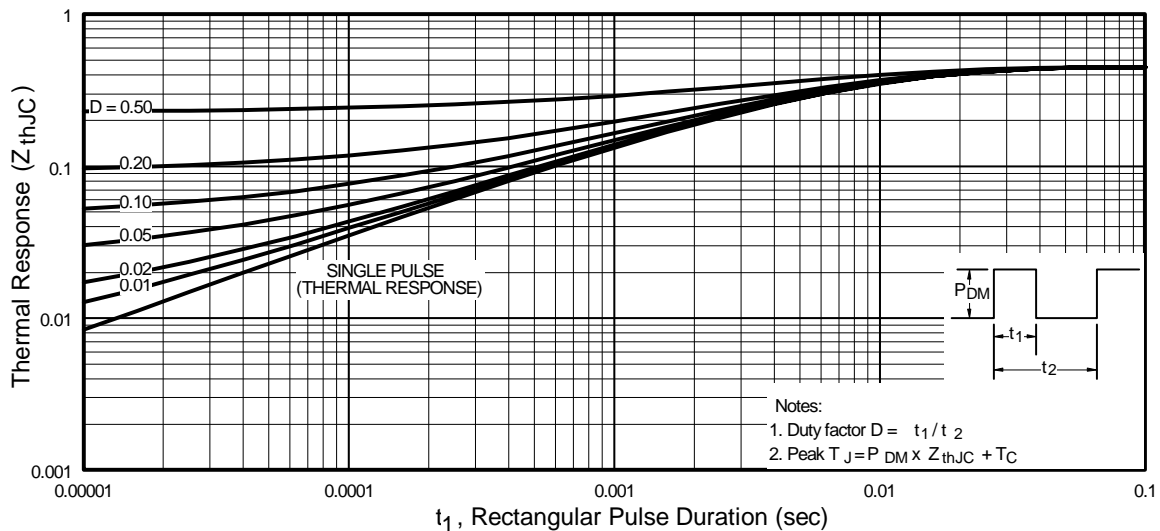
**Fig 9.** Maximum Drain Current Vs. Case Temperature



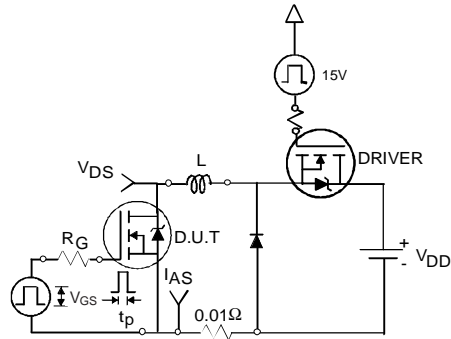
**Fig 10a.** Switching Time Test Circuit



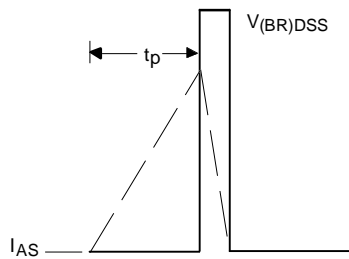
**Fig 10b.** Switching Time Waveforms



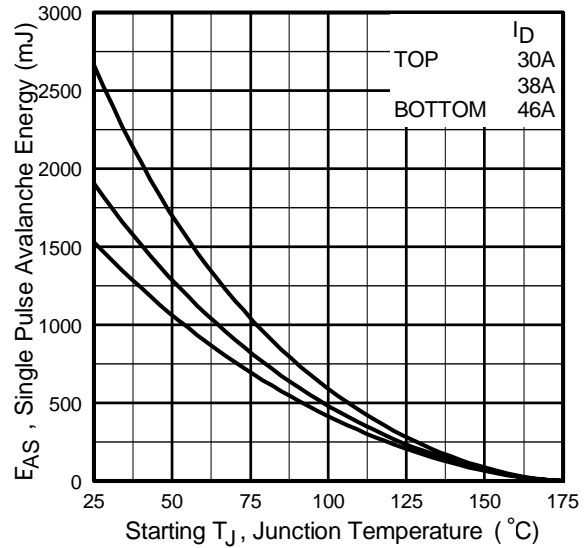
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



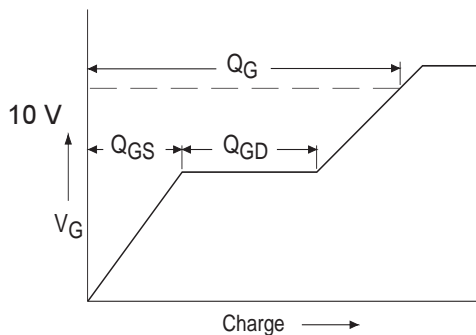
**Fig 12a.** Unclamped Inductive Test Circuit



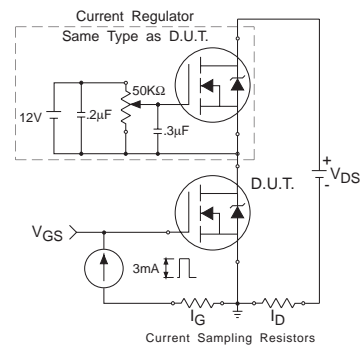
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

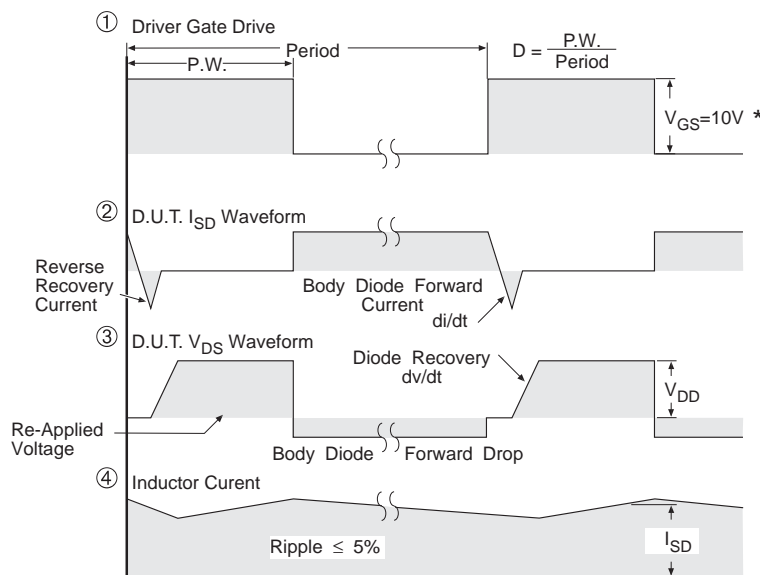
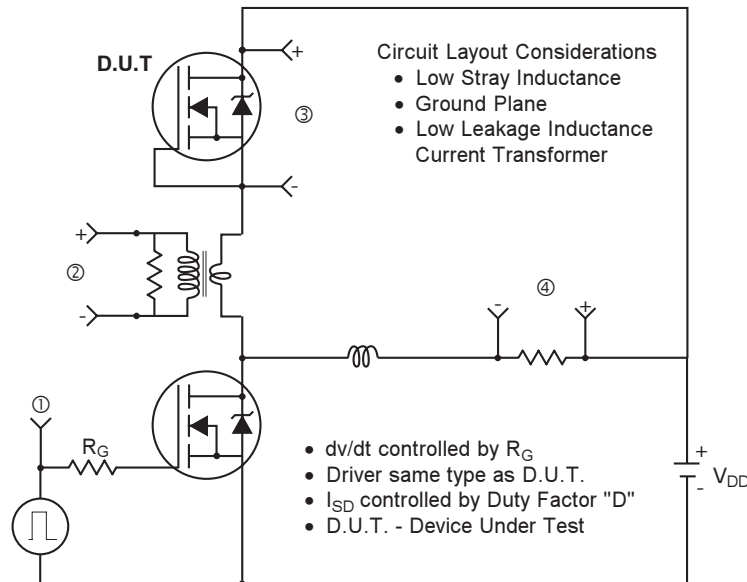


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

### Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

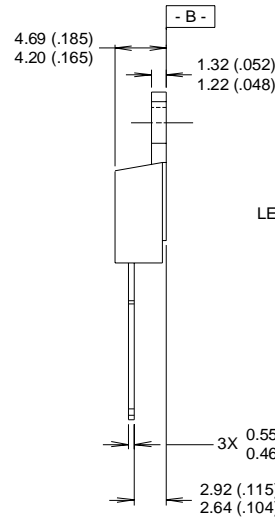
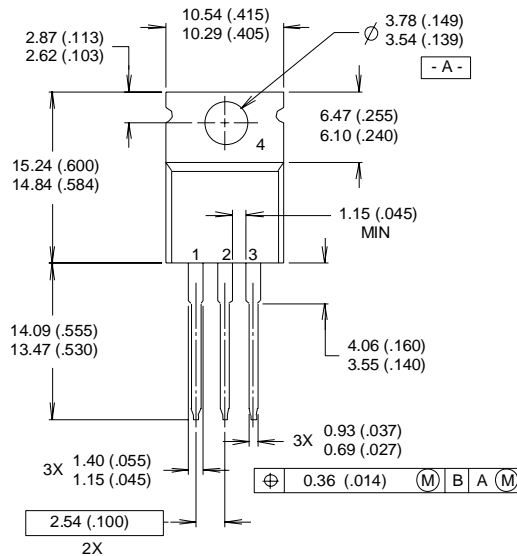
**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRL3713/S/L

International  
**IR** Rectifier

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS  
1 - GATE  
2 - DRAIN  
3 - SOURCE  
4 - DRAIN

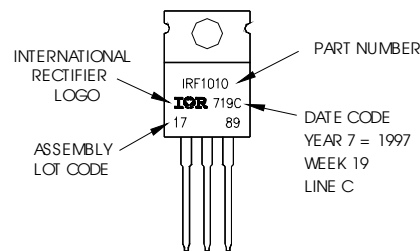
### NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

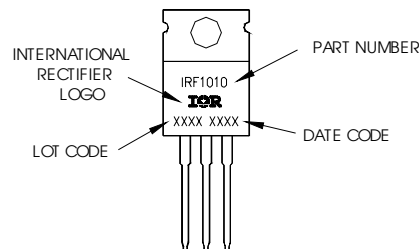
## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"



### For GB Production

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"

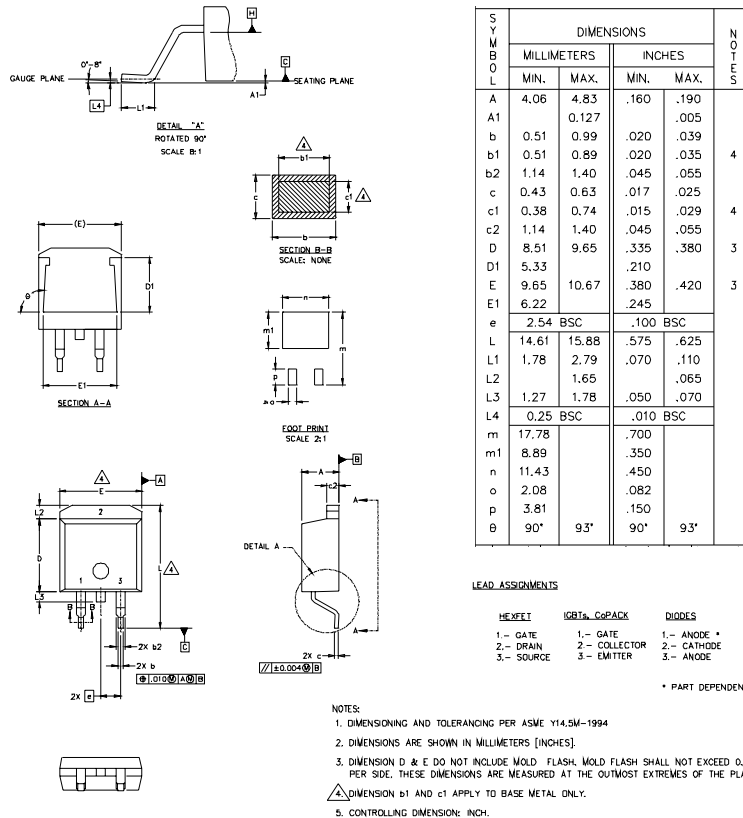




## D<sup>2</sup>Pak Package Outline

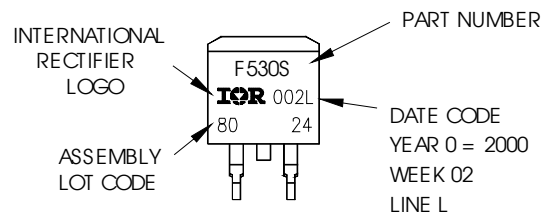
Dimensions are shown in millimeters (inches)

IRL3713/S/L



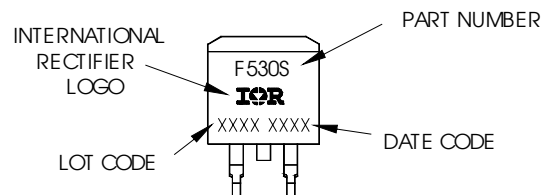
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW02, 2000  
IN THE ASSEMBLY LINE "L"



For GB Production

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW02, 2000  
IN THE ASSEMBLY LINE "L"

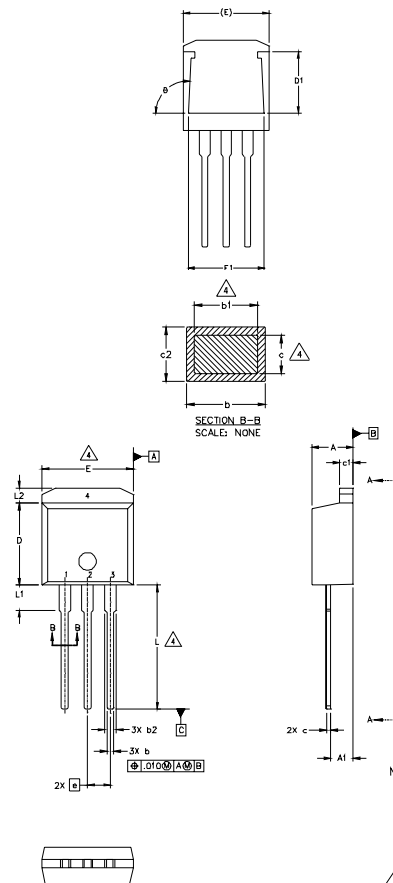


# IRL3713/S/L

International  
**IR** Rectifier

## TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

#### IGBT

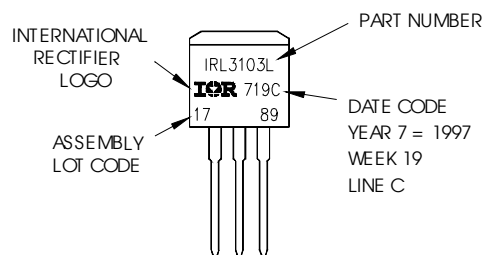
- 1- GATE
- 2- COLLECTOR

#### NOTES:

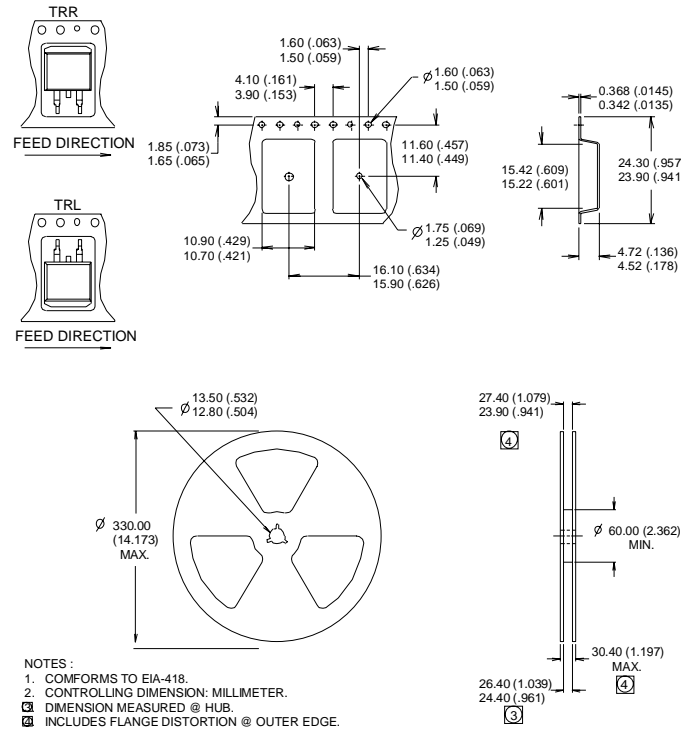
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"



## D<sup>2</sup>Pak Tape & Reel Information



### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1.4\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 46\text{A}$ ,  $V_{GS} = 10\text{V}$
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ This is only applied to TO-220A package
- ⑤ This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑦  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
IR Rectifier

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TAC Fax: (310) 252-7903

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